

## Abstract

### Integrated semiconductor structure

The invention relates to an integrated semiconductor structure, having a substrate (1), at least one semiconductor element (2) located on the substrate (1), a pad metal (3) having a surface (F), a multiplicity of metal layers (4.x) which are located between the pad metal (3) and the substrate (1), and a multiplicity of insulation layers (5.y), which separate the metal layers (4.x) from one another, the pad metal (3) extending at least over part of the at least one semiconductor element (2).

The invention is distinguished by the fact that, below the surface (F) of the pad metal (3), at least the top two metal layers (4.x, 4.x-1) have a structure which in each case at least includes two adjacent interconnects (4.x.z, 4.x-1.z).

Fig. 1